

Dual N-Channel Enhancement Mode MOSFET

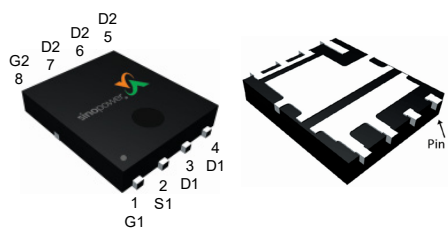
Features

- Channel 1**
 30V/90A
 $R_{DS(ON)} = 4.1m\Omega(max.) @ V_{GS} = 10V$
 $R_{DS(ON)} = 6m\Omega(max.) @ V_{GS} = 4.5V$
- Channel 2**
 30V/198A
 $R_{DS(ON)} = 1.4m\Omega(max.) @ V_{GS} = 10V$
 $R_{DS(ON)} = 2.2m\Omega(max.) @ V_{GS} = 4.5V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- Moisture Sensitivity Level MSL1 (per JEDEC J-STD-020D)

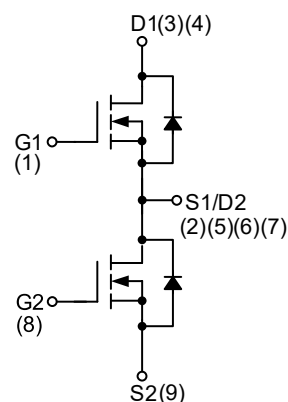
Applications

- Power Management in Desktop Computer or DC/DC Converters.

Pin Description



DFN5x6J-8_EP2



N-Channel MOSFET

Ordering and Marking Information

SM7346EQ - Assembly Material Handling Code Temperature Range Package Code	Package Code KP : DFN5x6J-8_EP2 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel Assembly Material G : Halogen and Lead Free Device
SM7346EQ KP :  7346EQ XXXXX	XXXXXX - Lot Code

Note : SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the leadfree requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Channel 1	Channel 2	Unit
Common Ratings					
V_{DSS}	Drain-Source Voltage		30		V
V_{GSS}	Gate-Source Voltage		± 20	± 20	V
T_J	Maximum Junction Temperature		150		$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range		-55 to 150		$^{\circ}\text{C}$
I_S	Diode Continuous Forward Current	$T_C=25^{\circ}\text{C}$	45	81	A
I_D	Continuous Drain Current	$T_C=25^{\circ}\text{C}$	90	198	A
		$T_C=100^{\circ}\text{C}$	57	125	
I_{DM}^{a}	Pulse Drain Current	$T_C=25^{\circ}\text{C}$	358	400	A
P_D	Maximum Power Dissipation	$T_C=25^{\circ}\text{C}$	54	89	W
		$T_C=100^{\circ}\text{C}$	22	36	
$R_{\theta\text{JC}}$	Thermal Resistance-Junction to Case	Steady State	2.3	1.4	$^{\circ}\text{C}/\text{W}$
I_D	Continuous Drain Current	$T_A=25^{\circ}\text{C}$	16	29	A
		$T_A=70^{\circ}\text{C}$	13	23	
I_{DM}^{a}	Pulse Drain Current	$T_A=25^{\circ}\text{C}$	63	115	A
P_D	Maximum Power Dissipation	$T_A=25^{\circ}\text{C}$	1.7	1.9	W
		$T_A=70^{\circ}\text{C}$	1.1	1.2	
$R_{\theta\text{JA}}^{\text{b}}$	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	35	30	$^{\circ}\text{C}/\text{W}$
		Steady State	75	66	
I_{AS}^{c}	Avalanche Current, Single pulse	$L=0.1\text{mH}$	22	40	A
E_{AS}^{c}	Avalanche Energy, Single pulse	$L=0.1\text{mH}$	24	80	mJ

Note a : Pulse width is limited by maximum junction temperature.

Note b : Surface mounted on 1in^2 pad area, steady state $t = 999\text{s}$.

Note c : UIS tested and pulse width are limited by maximum junction temperature (initial temperature $T_J=25^{\circ}\text{C}$).

Channel 1 Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Channel 1			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.2	1.6	2	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =15A	-	3.4	4.1	mΩ
		T _J =125°C	-	4.8	-	
		V _{GS} =4.5V, I _{DS} =12A	-	4.6	6	
Gfs	Forward Transconductance	V _{DS} =5V, I _{DS} =8A	-	25	-	S
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =8A, V _{GS} =0V	-	0.75	1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =15A, dI _{SD} /dt=100A/μs	-	25	-	ns
t _a	Charge Time		-	12	-	
t _b	Discharge Time		-	13	-	
Q _{rr}	Reverse Recovery Charge		-	11	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	1.7	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz	-	930	1209	pF
C _{oss}	Output Capacitance		-	430	-	
C _{rss}	Reverse Transfer Capacitance		-	35	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, R _L =15Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	12	22	ns
t _r	Turn-on Rise Time		-	11	20	
t _{d(OFF)}	Turn-off Delay Time		-	24	44	
t _f	Turn-off Fall Time		-	18	33	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =15A	-	13	18	nC
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _{DS} =15A	-	5.8	-	
Q _{gth}	Threshold Gate Charge		-	1.4	-	
Q _{gs}	Gate-Source Charge		-	2.7	-	
Q _{gd}	Gate-Drain Charge		-	1.1	-	

Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Note e : Guaranteed by design, not subject to production testing.

Channel 2 Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

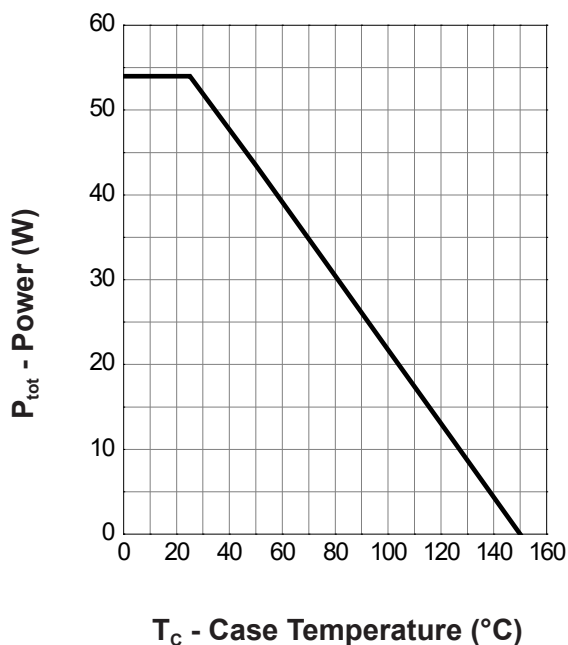
Symbol	Parameter	Test Conditions	Channel 2			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.2	1.6	2	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =25A	-	1.2	1.4	mΩ
		T _J =125°C	-	1.7	-	
		V _{GS} =4.5V, I _{DS} =20A	-	1.7	2.2	
Gfs	Forward Transconductance	V _{DS} =5V, I _{DS} =20A	-	60	-	S
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =13A, V _{GS} =0V	-	0.75	1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =25A, dI _{SD} /dt=100A/μs	-	38	-	ns
t _a	Charge Time		-	20	-	
t _b	Discharge Time		-	18	-	
Q _{rr}	Reverse Recovery Charge		-	23	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	1.2	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz	-	2550	3315	pF
C _{oss}	Output Capacitance		-	1120	-	
C _{rss}	Reverse Transfer Capacitance		-	70	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, R _L =15Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	17	31	ns
t _r	Turn-on Rise Time		-	10	18	
t _{d(OFF)}	Turn-off Delay Time		-	47	85	
t _f	Turn-off Fall Time		-	51	92	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =25A	-	31	43.4	nC
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _{DS} =25A	-	14	-	
Q _{gth}	Threshold Gate Charge		-	3.1	-	
Q _{gs}	Gate-Source Charge		-	5.2	-	
Q _{gd}	Gate-Drain Charge		-	3	-	

Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

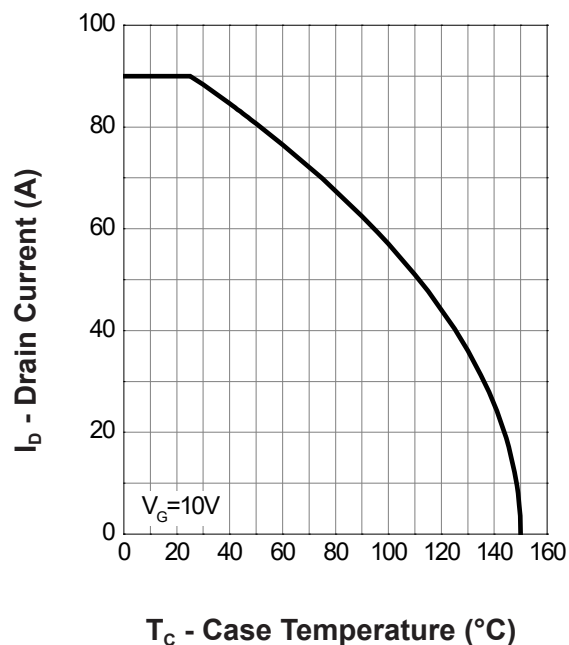
Note e : Guaranteed by design, not subject to production testing.

Channel 1 Typical Operating Characteristics

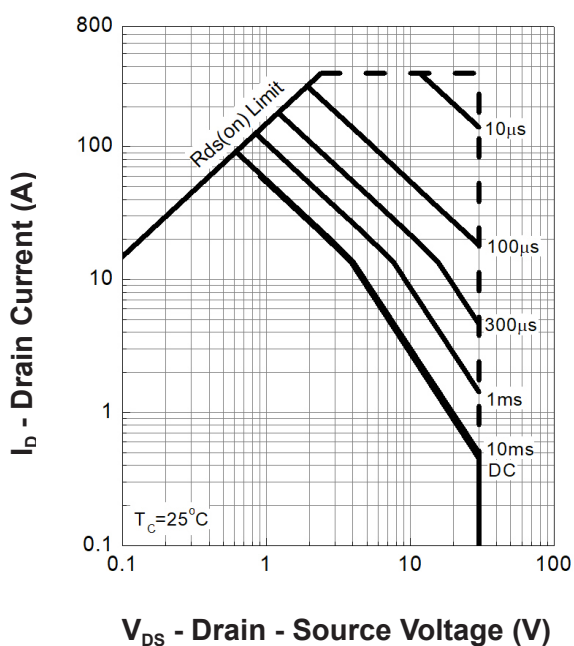
Power Dissipation



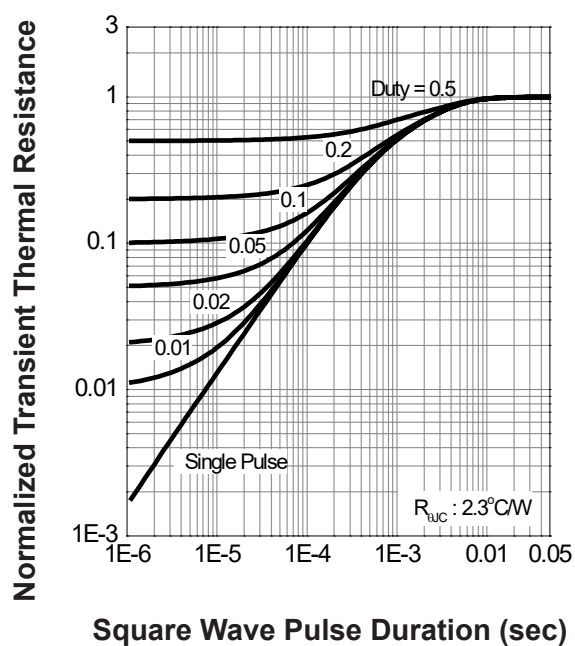
Drain Current



Safe Operation Area

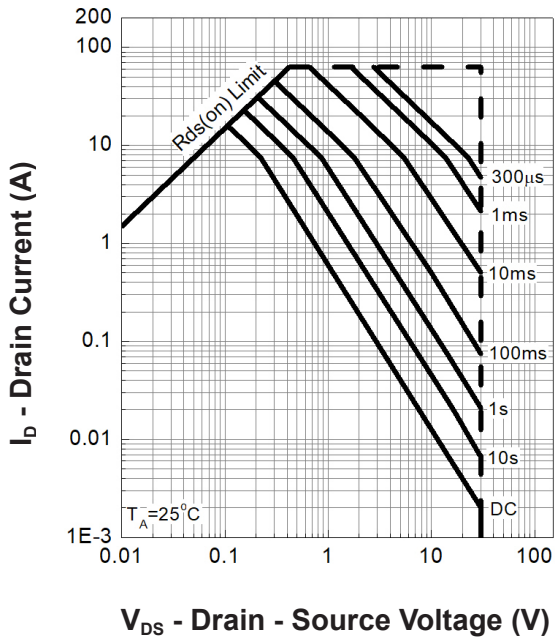


Thermal Transient Impedance

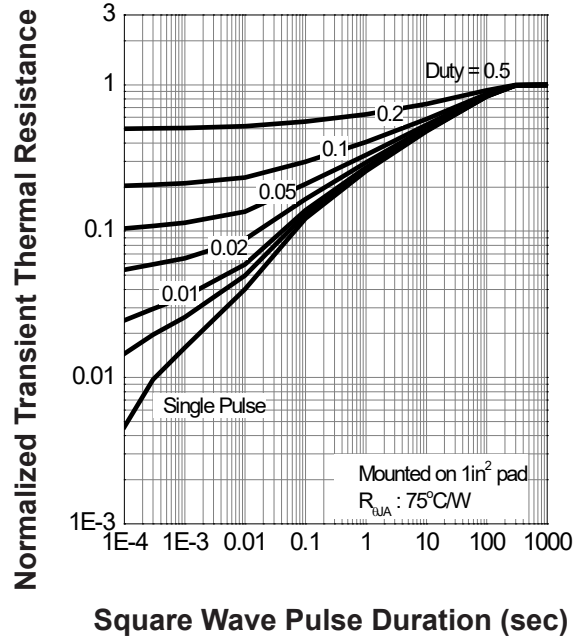


Channel 1 Typical Operating Characteristics(Cont.)

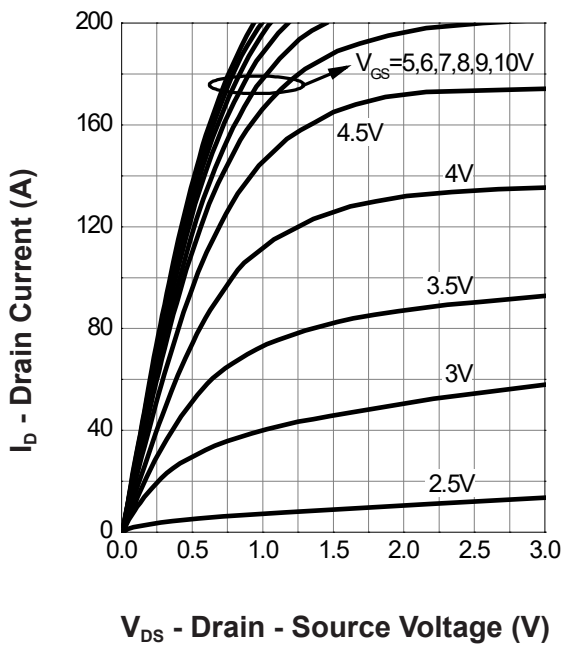
Safe Operation Area



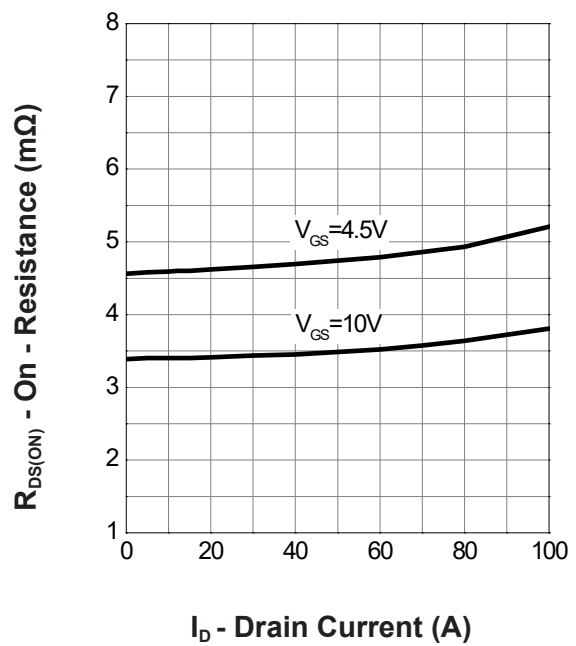
Thermal Transient Impedance



Output Characteristics

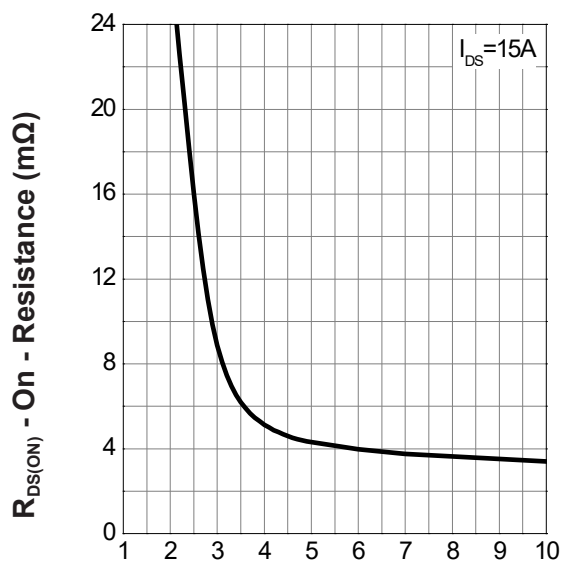


Drain-Source On Resistance

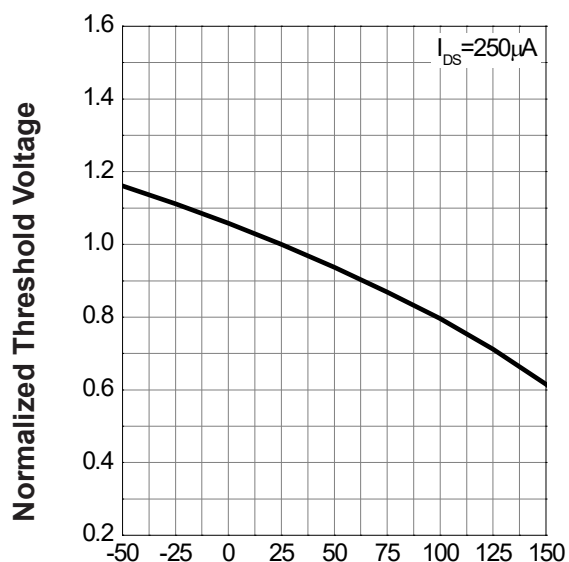


Channel 1 Typical Operating Characteristics(Cont.)

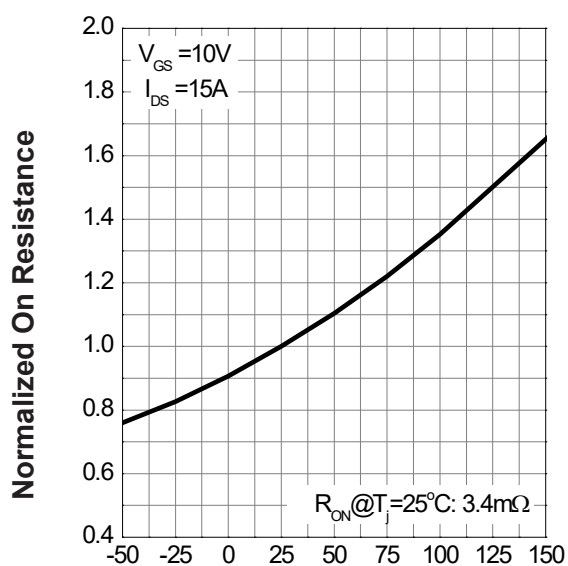
Gate-Source On Resistance

 V_{GS} - Gate - Source Voltage (V)

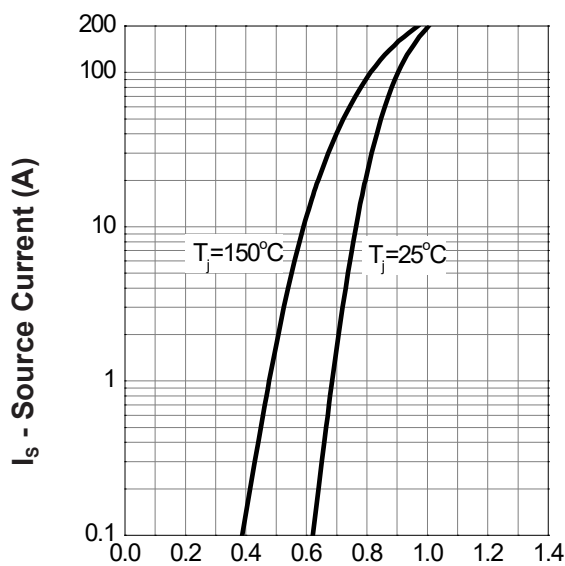
Gate Threshold Voltage

 T_J - Junction Temperature (°C)

Drain-Source On Resistance

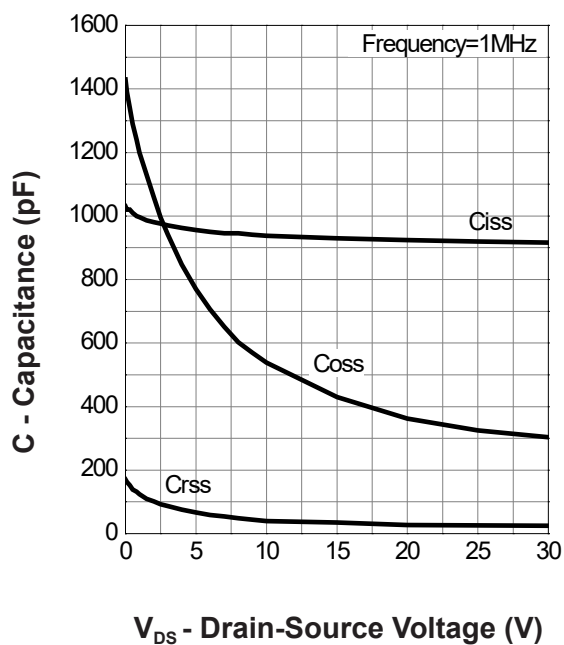
 T_J - Junction Temperature (°C)

Source-Drain Diode Forward

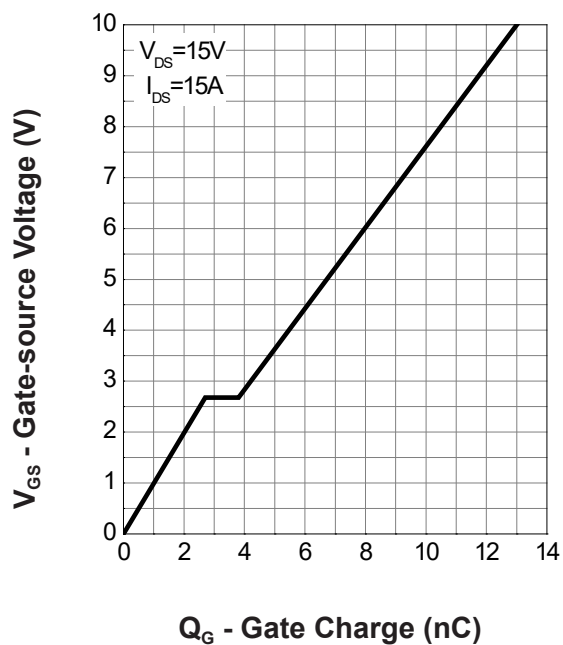
 V_{SD} - Source - Drain Voltage (V)

Channel 1 Typical Operating Characteristics(Cont.)

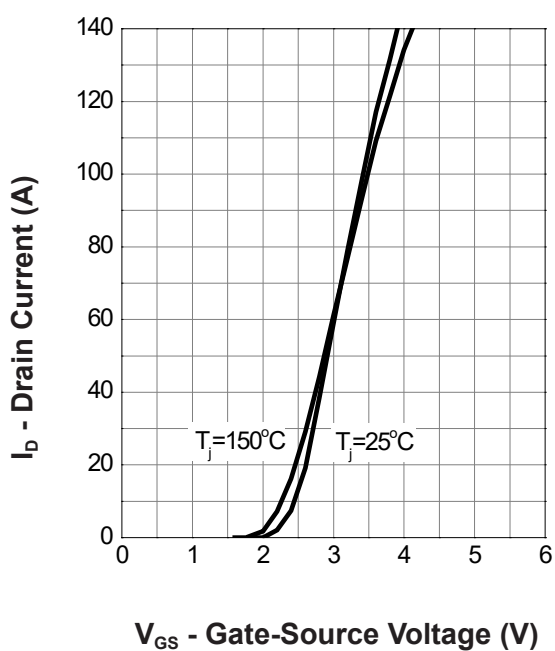
Capacitance



Gate Charge

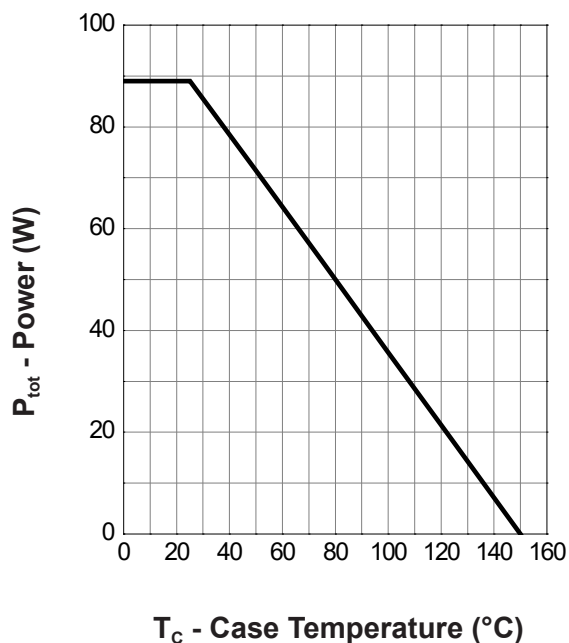


Transfer Characteristics

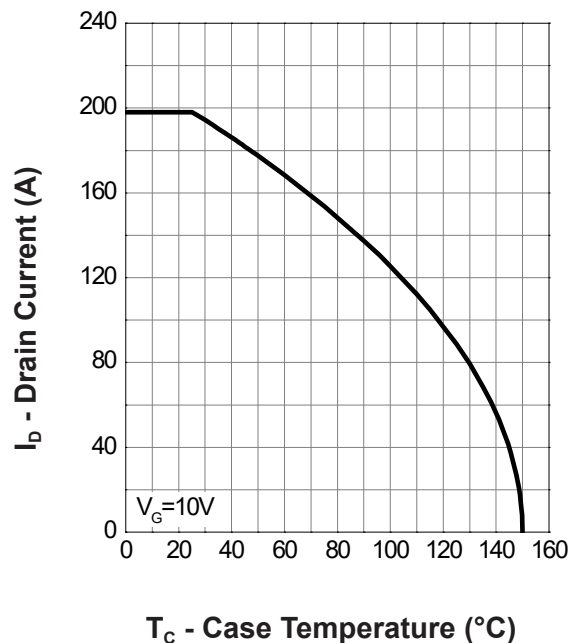


Channel 2 Typical Operating Characteristics

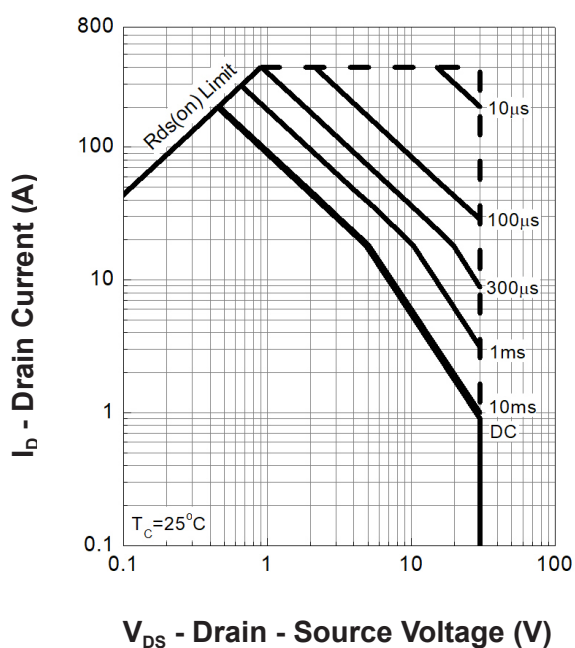
Power Dissipation



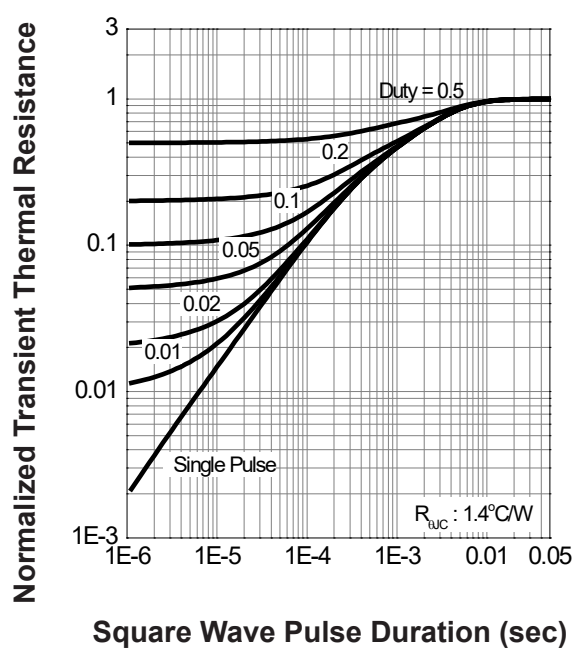
Drain Current



Safe Operation Area

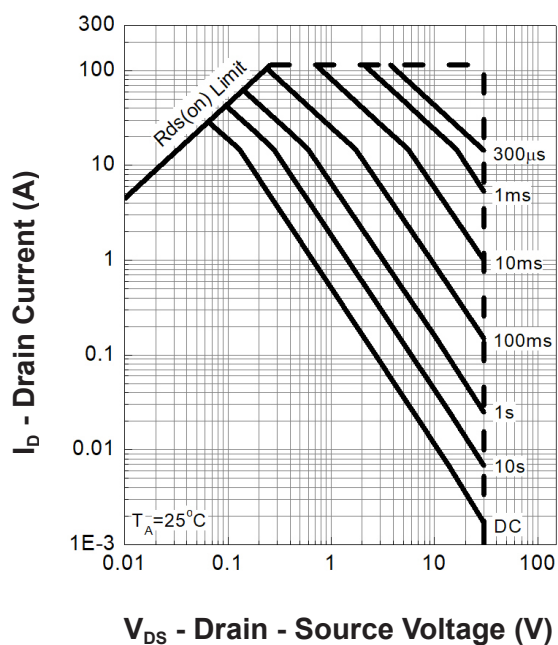


Thermal Transient Impedance

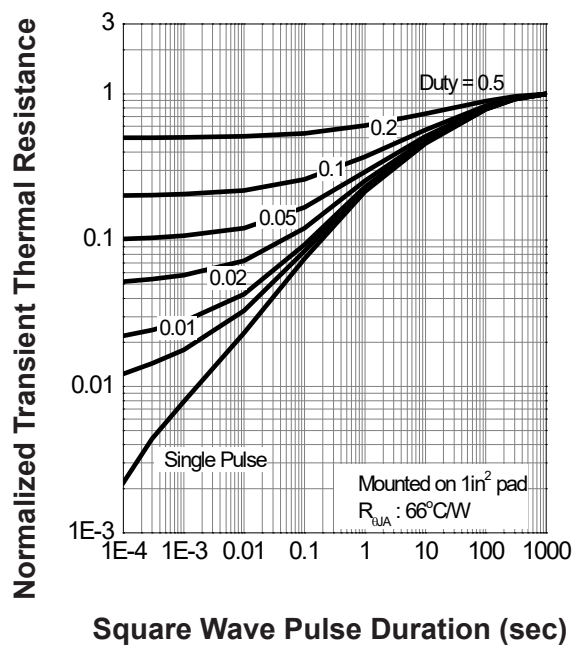


Channel 2 Typical Operating Characteristics(Cont.)

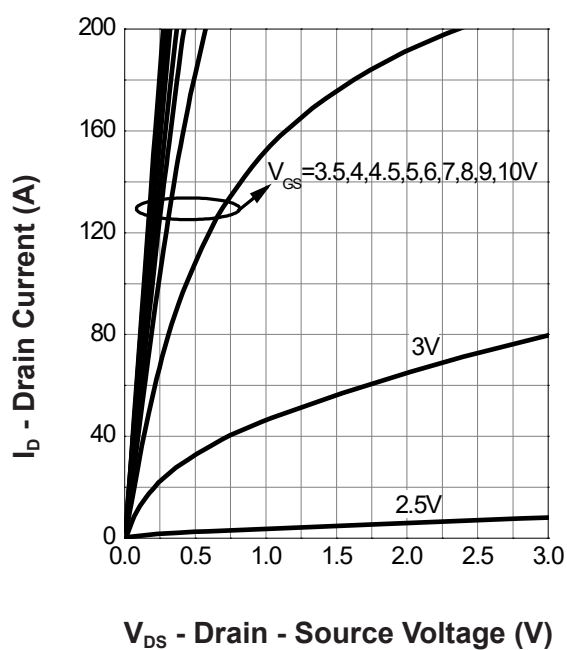
Safe Operation Area



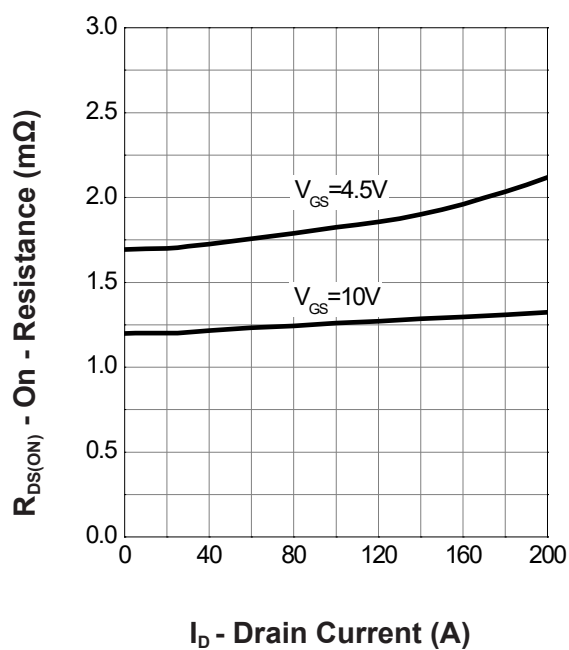
Thermal Transient Impedance



Output Characteristics

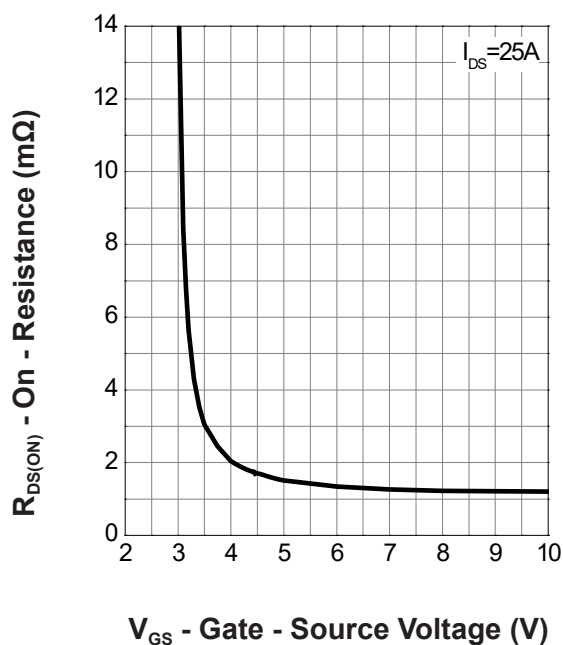


Drain-Source On Resistance

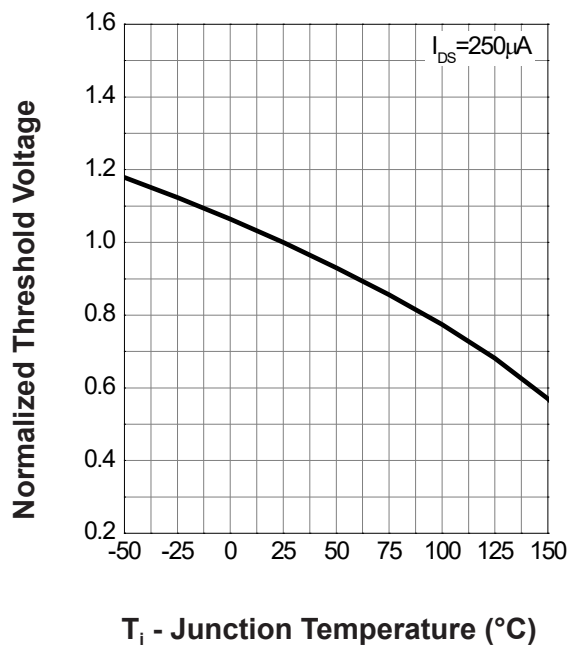


Channel 2 Typical Operating Characteristics(Cont.)

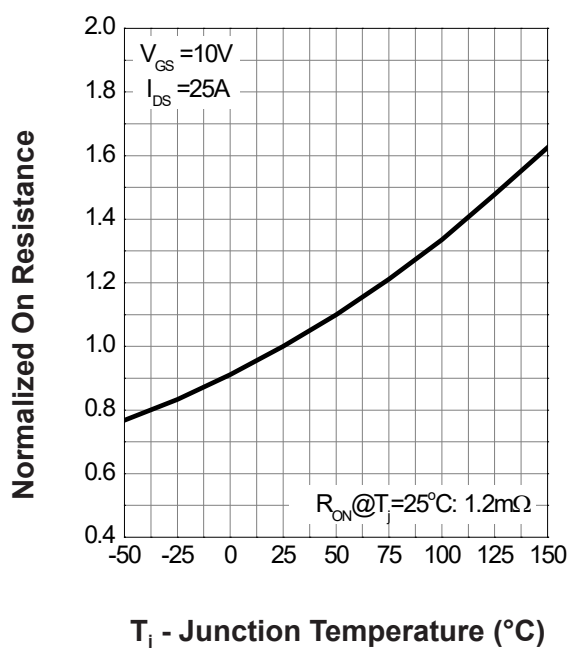
Gate-Source On Resistance



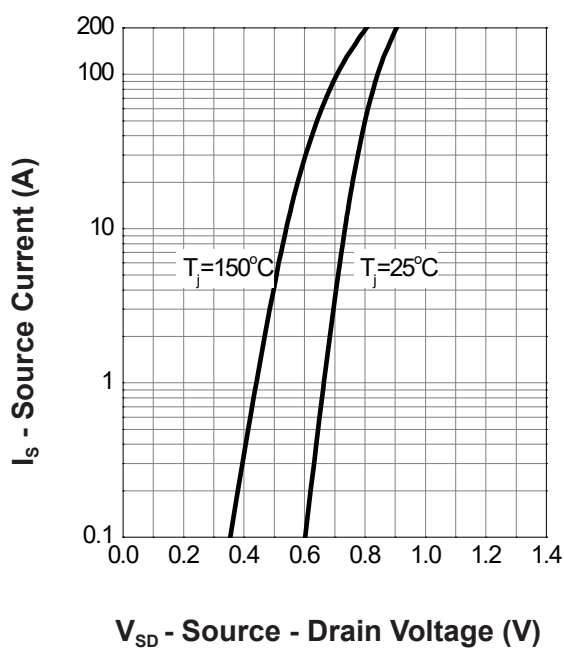
Gate Threshold Voltage



Drain-Source On Resistance

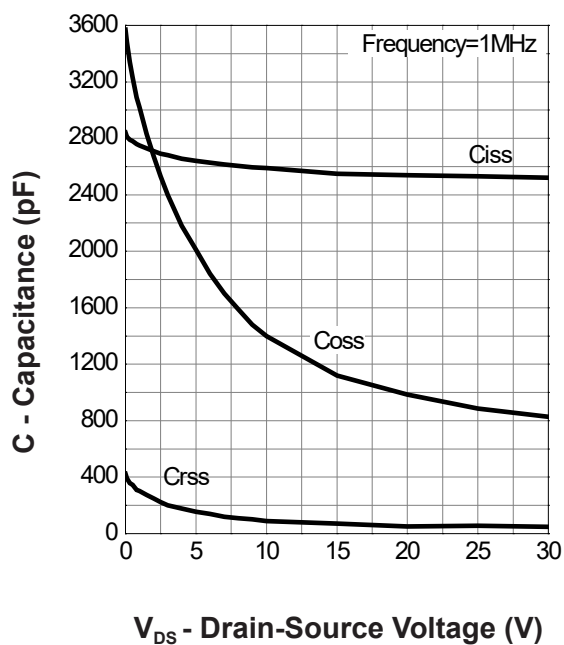


Source-Drain Diode Forward

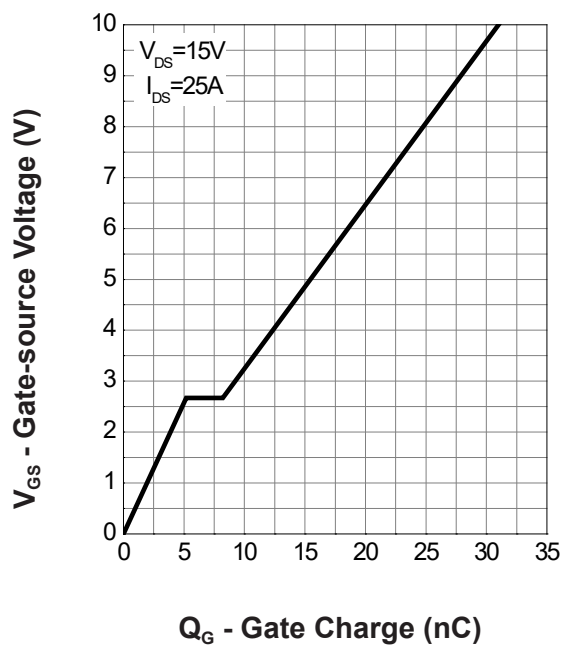


Channel 2 Typical Operating Characteristics(Cont.)

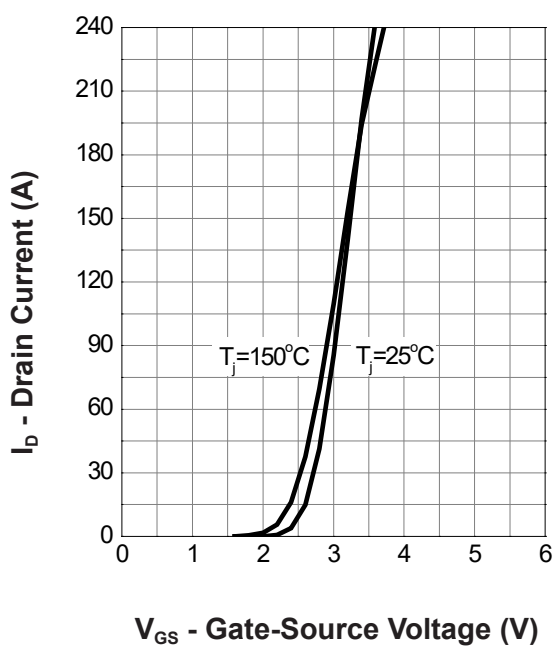
Capacitance



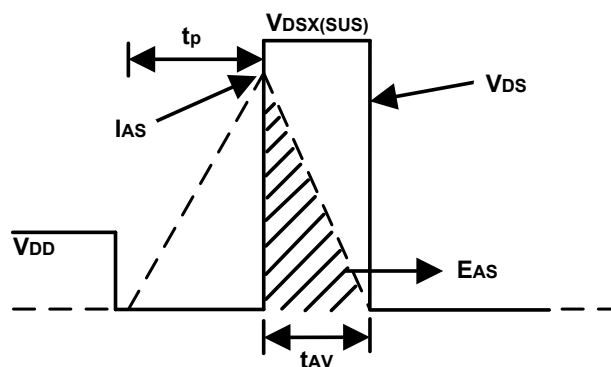
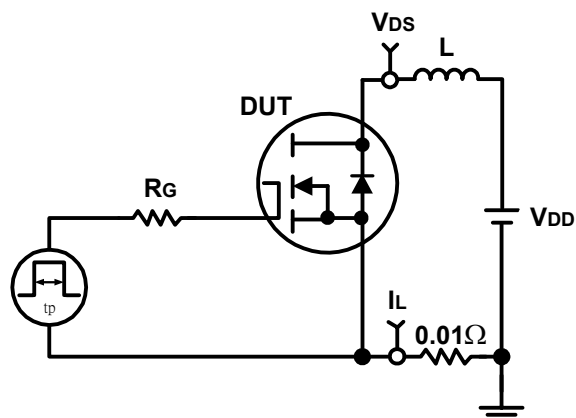
Gate Charge



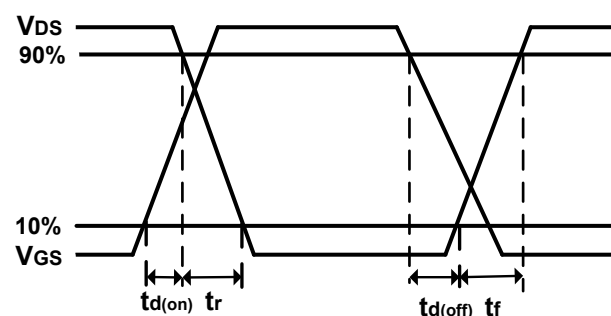
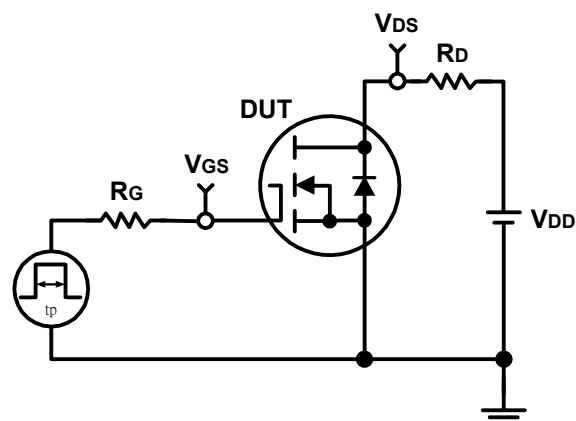
Transfer Characteristics



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



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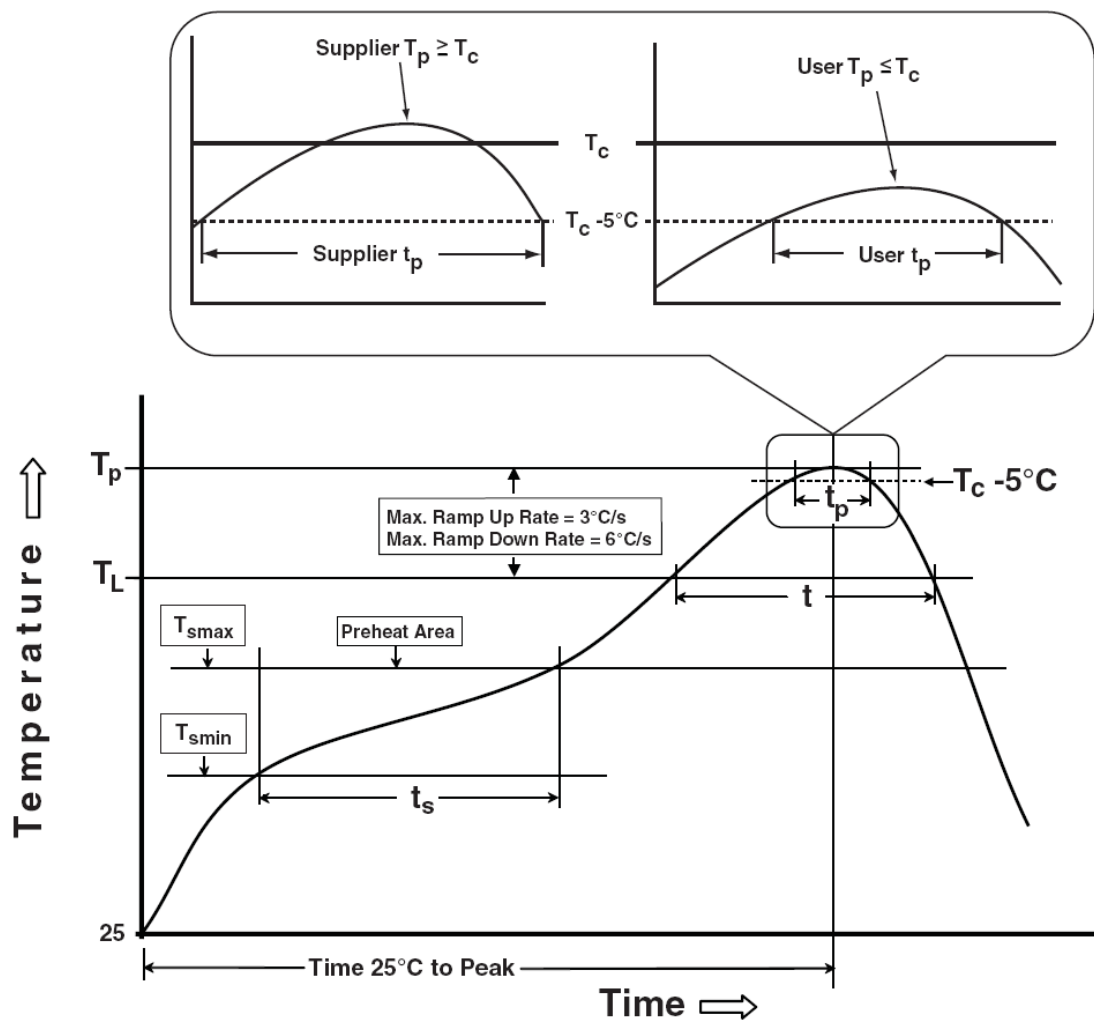
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Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Customer Service

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